

## **Description**

The IPD90P03P4L-04 uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})}$ , low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



 $V_{DS} = -30V$   $I_{D} = -120A$ 

 $R_{DS(ON)}$  <4.5m $\Omega$  @  $V_{GS}$ =-10V

### **Application**

Lithium battery protection

Wireless impact

Mobile phone fast charging

## **Package Marking and Ordering Information**

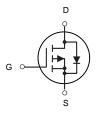
| Product ID     | Pack      | Marking    | Qty(PCS) |  |
|----------------|-----------|------------|----------|--|
| IPD90P03P4L-04 | TO-252-2L | 90P03 XXXX | 2500     |  |

### Absolute Maximum Ratings (TC=25℃unless otherwise noted)

| Symbol   | Parameter                                       | Max.                | Units |
|----------|---|---------------------|-------|
| VDSS     | Drain-Source Voltage                            | -30                 | V     |
| VGSS     | Gate-Source Voltage                             | ±20                 | V     |
| ID       | Continuous Drain Current T <sub>C</sub> = 25°C  | -120                | А     |
| ID       | Continuous Drain Current T <sub>C</sub> = 100 ℃ | -80                 | А     |
| IDM      | Pulsed Drain Current note1                      | -470                | А     |
| EAS      | Single Pulsed Avalanche Energy note2            | 580                 | mJ    |
| PD       | Power Dissipation $T_C$ = 25 $^{\circ}$ C       | 100                 | W     |
| RθJC     | Thermal Resistance, Junction to Case 1.4        |                     | °C/W  |
| TJ, TSTG | Operating and Storage Temperature Range         | e Range -55 to +175 |       |



TO-252-2L



P-Channel MOSFET



## Electrical Characteristics (TJ=25℃ unless otherwise noted)

| Symbol              | Parameter                         | Conditions   | Min   | Тур  | Max  | Unit |
|---------------------|-----------------------------------|--|-------|------|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage    | V <sub>GS</sub> =0V I <sub>D</sub> =-250μA                         | -30   |      |      | V    |
| IDSS                | Zero Gate Voltage Drain Current   | V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V                         |       |      | -1   | μA   |
| Igss                | Gate-Body Leakage Current         | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                         | os=0V |      | ±100 | nA   |
| V <sub>GS(th)</sub> | Gate Threshold Voltage            | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA -1       |       | -1.7 | -2.5 | V    |
| <b>g</b> FS         | Forward Transconductance          | V <sub>DS</sub> =-5V, I <sub>D</sub> =-20A                         |       | 65   |      | S    |
| D.                  | Drain-Source On-State Resistance  | V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A                        |       | 3.7  | 4.5  | mΩ   |
| RDS(ON)             |                                   | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-20A                       |       | 6    | 8.2  | mΩ   |
| Ciss                | Input Capacitance                 |  |       | 7000 |      | pF   |
| Coss                | Output Capacitance                | V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V,<br>f=1.0MHz            |       | 820  |      | pF   |
| Crss                | Reverse Transfer Capacitance      |  |       | 540  |      | pF   |
| Rg                  | Gate resistance                   | V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1.0MHz                 |       | 2.2  |      | Ω    |
| t <sub>d(on)</sub>  | Turn-on Delay Time                |  |       | 14   |      | nS   |
| tr                  | Turn-on Rise Time                 | V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V,                      |       | 13   |      | nS   |
| t <sub>d(off)</sub> | Turn-Off Delay Time               | RL=0.75 $\Omega$ , R <sub>GEN</sub> =3 $\Omega$                    |       | 65   |      | nS   |
| t <sub>f</sub>      | Turn-Off Fall Time                |  |       | 37   |      | nS   |
| Qg                  | Total Gate Charge                 |  |       | 130  |      | nC   |
| Qgs                 | Gate-Source Charge                | V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-20A |       | 12   |      | nC   |
| $Q_{gd}$            | Gate-Drain Charge                 |  |       | 31   |      | nC   |
| Isp                 | Source-Drain Current (Body Diode) |  |       |      | -108 | Α    |
| VsD                 | Forward on Voltage (Note 3)       | V <sub>GS</sub> =0V, I <sub>S</sub> =-20A                          |       |      | -1.2 | V    |
| t <sub>rr</sub>     | Reverse Recovery Time             | I <sub>F</sub> =-20A, di/dt=100A/μs                                |       | 30   |      | ns   |
| Qrr                 | Reverse Recovery Charge           | I <sub>F</sub> =-20A, di/dt=100A/μs                                |       | 40   |      | nC   |

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 2.E<sub>AS</sub> condition:  $T_J$ =25  $^{\circ}$ C, $V_{DD}$ =15V, $V_G$ =-10V, Rg=25 $\Omega$ , L=0.5mH.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



# **Typical Electrical And Thermal Characteristics (Curves)**

Figure 1. Output Characteristics

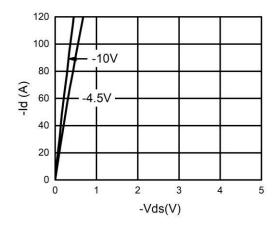


Figure 2. Transfer Characteristics

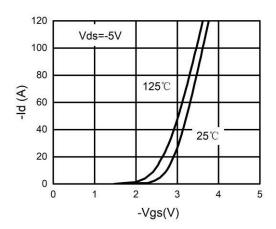


Figure 3. Power Dissipation

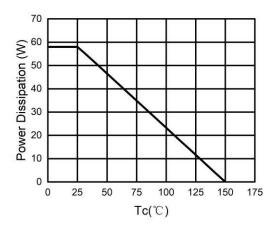


Figure 4. Drain Current

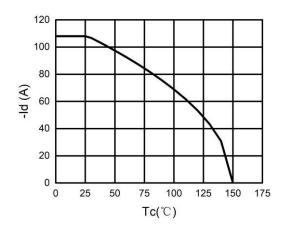


Figure 5. BV<sub>DSS</sub> vs Junction Temperature

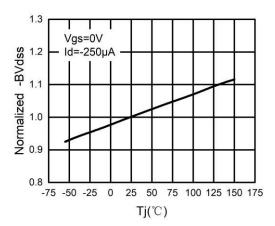


Figure 6. R<sub>DS(ON)</sub> vs Junction Temperature

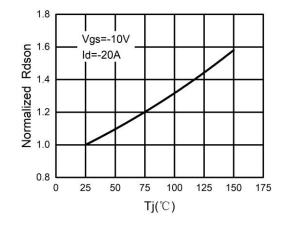


Figure 7. Gate Charge Waveforms

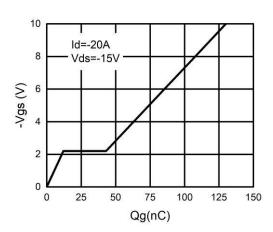


Figure 8. Capacitance

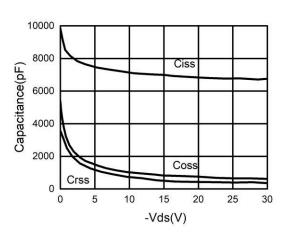


Figure 9. Body-Diode Characteristics

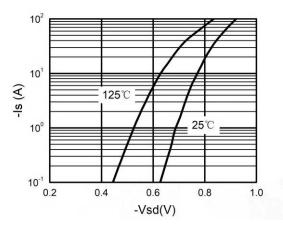
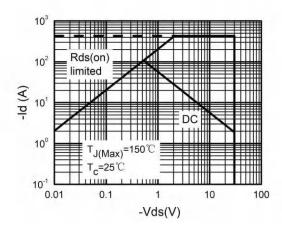
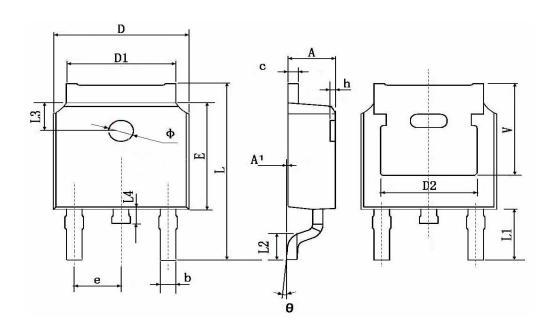


Figure 10. Maximum Safe Operating Area



# **TO-252-2L Package Information**



| Symbol | Dimensions | In Millimeters        | Dimension  | s In Inches |
|--------|------------|-----------------------|------------|-------------|
|        | Min.       | Max.                  | Min.       | Max.        |
| A      | 2.200      | 2.400                 | 0.087      | 0.094       |
| A1     | 0.000      | 0.127                 | 0.000      | 0.005       |
| b      | 0.660      | 0.860                 | 0.026      | 0.034       |
| С      | 0.460      | 0.580                 | 0.018      | 0.023       |
| D      | 6.500      | 6.700                 | 0.256      | 0.264       |
| D1     | 5.100      | 5.460                 | 0.201      | 0.215       |
| D2     | 4.830      | 4.830 TYP.            |            | TYP.        |
| E      | 6.000      | 6.200                 | 0.236      | 0.244       |
| е      | 2.186      | 2.386                 | 0.086      | 0.094       |
| L      | 9.800      | 10.400                | 0.386      | 0.409       |
| L1     | 2.900 TYP. |                       | 0.114 TYP. |             |
| L2     | 1.400      | 1.700                 | 0.055      | 0.067       |
| L3     | 1.600 TYP. |                       | 0.063 TYP. |             |
| L4     | 0.600      | 1.000                 | 0.024      | 0.039       |
| Ф      | 1.100      | 1.300                 | 0.043      | 0.051       |
| θ      | 0°         | 8°                    | 0°         | 8°          |
| h      | 0.000      | 0.300                 | 0.000      | 0.012       |
| V      | 5.350      | 5.350 TYP. 0.211 TYP. |            | TYP.        |



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